App. Serial No.: 10/017,458
Atty. Docket No.: 0011-051

IN THE CLAIMS

Please amend the claims as follows:

1. (currently amended) A method for creating a dummy metal fill pattern near functional circuitry, comprising:

creating a margin area around the functional circuitry;

selecting a dummy metal fill pattern of alternative functional circuitry, wherein the alternative functional circuitry is a selected portion of functional circuitry from a metal layer on which the dummy metal fill pattern is to be used;

trimming the dummy metal fill pattern to the margin area to create a trimmed fill pattern; and

overlaying said trimmed fill pattern and the functional circuitry.

2. (previously amended) The method for creating a dummy metal fill pattern of claim 1, and further including:

removing excess metal from the dummy metal fill pattern.

3. (original) The method for creating a dummy metal fill pattern of claim 2, wherein:

the excess metal is at least one metal sliver.

4. (previously amended) The method for creating a dummy metal fill pattern of claim 3, wherein:

the metal sliver is a thin strip of metal created when the margin area is removed from the dummy metal fill pattern.

Claim 5 (canceled)

6. (previously amended) The method for creating a dummy metal fill pattern of claim 1, wherein:

the alternative functional circuitry is selected to be alike to that near the functional circuitry.

7. (canceled)

8. (original) The method for creating a dummy metal fill pattern of claim 1, wherein:
the dummy metal fill pattern is created on a metal layer of an LCOS array.

9. (original) The method for creating a dummy metal fill pattern of claim 1, wherein:
the dummy metal fill pattern is created on a layer under a mirror layer of an LCOS array.

10. (original) The method for creating a dummy metal fill pattern of claim 1, wherein:
the dummy metal fill pattern is created on a layer of a reflective LCOS array.

11. (canceled)

12. (canceled)

13. (original) The method for creating a dummy metal fill pattern of claim 1, wherein:
said margin area is created by growing the area of the functional circuitry.

14-22. (canceled)

23. (currently amended) A method for providing dummy fill in a LCOS array, comprising:
selecting a metal fill pattern from functional circuitry on a layer of the array <u>on which the metal fill pattern is to be used</u>; and
filling an unfilled area with the metal fill pattern.

24. (original) The method for providing dummy fill of claim 23, and further including:
filling a partially filled area with a portion of the metal fill pattern.

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26. (new) A method for providing dummy fill in a LCOS array, comprising:

selecting a metal fill pattern from functional circuitry on a layer of the array;

filling an unfilled area with the metal fill pattern; and

filling a partially filled area with a portion of the metal fill pattern.